R16 Code No: 131AK JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD B.Tech I Year I Semester Examinations, May/June - 2019 BASIC ELECTRICAL AND ELECTRONICS ENGINEERING (Common to EEE, ECE, CSE, EIE, IT, ETM)

Time: 3 hours

Max. Marks: 75

Note: This question paper contains two parts A and B.

Part A is compulsory which carries 25 marks. Answer all questions in Part A. Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have a, b, c as sub questions.



Determine v_0 and *i* in the circuit shown in figure 1. 1.a)



Figure: 1

Write the expressions for a delta-to-wye transformation. [3] b) [2] c). State the principle of superposition. What is the resonant frequency of a series RLC circuit where $R = 10\Omega$, L = 25 mH and d) [3] $C = 100 \mu F$? Evaluate the Q factor. [2] What is the current equation of diode? e)

- What is a junction capacitance of a diode? f)
- What is a bipolar junction transistor? g)
- What are the three types of configuration in transistors? h)
- Define pinch off voltage in FET. i)
- Sketch the basic structure of an N-Channel JFET. i)

PART-B

(50 Marks)

[3]

[2]

[3]

[2]

[3]

2.a) State and explain Kirchhoff's laws.

Calculate the equivalent resistance of the circuit shown in the figure 2. b)



[4+6]

- 3.a) Define average and effective value, RMS value for voltage signal with an example.
 - b) Use source transformation to determine the current and power absorbed by the 8Ω resistor as shown in figure 3. [5+5]



4.a) Derive the condition for resonant frequency of the given parallel circuit and define the band width and quality factor of a resonant circuit figure 4.





b) Find the Thevenin's equivalent looking into terminals a-b of the circuit in figure 5 and solve for i_x . [5+5]





5.a) Verify Reciprocity theorem of the given circuit shown in figure 6.



b) Find the Norton equivalent with respect to terminals a-b in the circuit shown in figure 7. [5+5]



- 6.a) Discuss the phenomenon of diffusion of charge carriers in semiconductors.
 b) How does a capacitor filter improve the response of a rectifier circuit? [5+5]
 OR
 7.a) Explain about Zener diode and its V I characteristics.
 b) Derive an expression for the rectification efficiency of a full-wave rectifier. [5+5]
- 8.a) Discuss about different operating regions of transistor.
 - b) Explain the input and output characteristics of a transistor in CE configuration. [5+5]

OR

- 9.a) Explain the two types of breakdown in transistors.
- b) Explain the input and output characteristics of a transistor in CB configuration. [5+5]
- 10.a) Explain the phenomenon of pinch off voltage in a FET with a neat diagram and write the expression for I_{DS} with respect to pinch off voltage.
 - b) Two identical FETs are connected in parallel. Derive an expression for its overall μ factor. [5+5]

OR

11.a) Write a note on biasing schemes of JFET.

b) Give the small signal equivalent circuit of a FET amplifier in CG configuration and derive the equation for voltage gain. [5+5]

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